

ABSTRACT OF THE DISCLOSURE

PROCESS FOR OBTAINING A THIN FILM, PARTICULARLY A
SEMICONDUCTING FILM, COMPRISING AN AREA PROTECTED FROM
IONS, AND INVOLVING AN IONIC IMPLANTATION STEP

The invention relates to a process for obtaining a thin film from a substrate, the film being delimited in the substrate by ionic implantation and by heat treatment inducing a fracture line along which the film
5 can be separated from the rest of the substrate. A particular area, for example composed of a grid oxide layer (15) and the channel area (19) of a MOS transistor (12) created in the substrate region (10) intended to form the thin film (20), this area may be
10 protected by ionic implantation by masking using the transistor grid (16), which does not prevent the fracture from occurring provided that the width of the area does not exceed a limiting dimension determined for the material forming the substrate.

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Figure 2.